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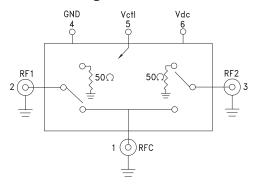


## Typical Applications

The HMC-C011 is ideal for:

- Basestation Infrastructure
- Fiber Optics & Broadband Telecom
- Microwave Radio & VSAT
- Military Radios, Radar, & ECM
- Test Instrumentation

## **Functional Diagram**



## GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 20 GHz

#### **Features**

High Isolation: >45 dB up to 5 GHz

>35 dB up to 20 GHz

Low Insertion Loss: 2 dB @ 12 GHz

2.5 dB @ 16 GHz

Fast Switching

Non-Reflective Design

Hermetically Sealed Module

Field Replaceable SMA connectors

-55 °C to +85 °C Operating Temperature

## **General Description**

The HMC-C011 is a general purpose broadband high isolation non-reflective GaAs MESFET SPDT switch housed in a miniature hermetic module with field replaceable SMA connectors. Covering DC to 20 GHz, the switch offers high isolation and low insertion loss. The switch features >45 dB isolation up to 5 GHz and >35 dB isolation up to 20 GHz. CMOS interface allows a single positive +5V bias voltage at very low DC currents.

## Electrical Specifications, $T_A = +25^{\circ}$ C, With Vdc = +5V & 0/+5V Control, 50 Ohm System

Parameter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss	DC - 4.0 GHz DC - 12.0 GHz DC - 16.0 GHz DC - 20.0 GHz		1.8 2.0 2.5 4.0	2.3 2.5 3.5 4.9	dB dB dB dB
Isolation	DC - 4.0 GHz DC - 8.0 GHz DC - 20.0 GHz	41 35 25	46 40 35		dB dB dB
Return Loss "On State"	DC - 12.0 GHz DC - 20.0 GHz		15 10		dB dB
Return Loss RF1, RF2 "Off State"	DC - 10.0 GHz DC - 15.0 GHz DC - 20.0 GHz		20 15 10		dB dB dB
Input Power for 1 dB Compression	0.5 - 20.0 GHz	20	23		dBm
Input Third Order Intercept (Two-Tone Input Power= +7 dBm Each Tone)	0.5 - 10.0 GHz 0.5 - 20.0 GHz		48 45		dBm dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	DC - 20 GHz		1.3 5.0		ns ns
Switching Transients	DC - 20 GHz		20		mVpp

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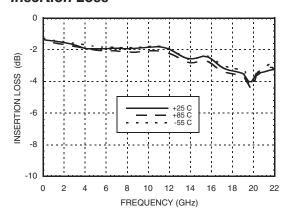


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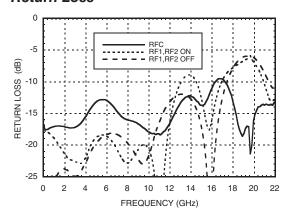


# GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 20 GHz

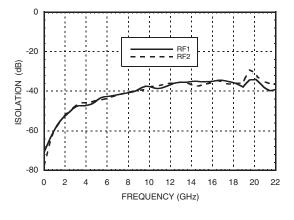
#### **Insertion Loss**



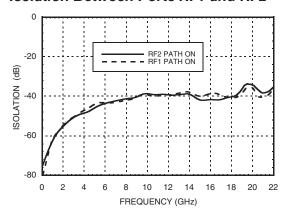
#### **Return Loss**



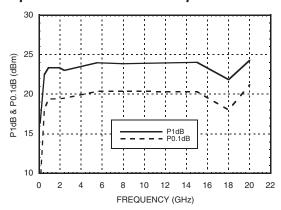
## Isolations



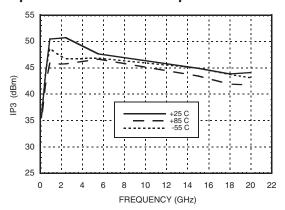
#### Isolation Between Ports RF1 and RF2



### Input P1dB & P0.1dB Compression Point



### Input Third Order Intercept Point





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# GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 20 GHz

## **Absolute Maximum Ratings**

RF Input Power	+27 dBm
Supply Voltage (Vdc)	+7 Vdc
Control Voltage Range (Vctl)	-0.5V to Vdd +0.5V
Hot Switch Power Level	+23 dBm
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C



## **Control Voltages**

State	Bias Condition	
High	+3.5 to Vdc @ 1 mA Typ.	
Low	0 to +1.5V @ 20 μA Typ.	

#### **Truth Table**

Control Input	Signal Path State		
Vctl	RFC to RF1	RFC to RF2	
High	On	Off	
Low	Off	On	

## Bias Voltage & Current

Vdc Range = +5 Vdc ± 10%		
Vdc (Vdc)	ldc (Typ.) (mA)	
+5.0	1.4	

(Bias current increases with switching rate to 15 - 20 mA.)

## **Pin Descriptions**

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Pin Number	Function	Description	Interface Schematic	
1, 2, 3	RFC, RF1, RF2	RF connector, SMA female, field replaceable. These pins are DC coupled and matched to 50 Ohms. DC blocking capacitors are required if external RF line potential is not equal to 0V.	RFC,RF1,RF2O	
4	GND	Power supply ground.	Ģ GND =	
5	Vctl	CMOS interface, control voltages per table. Requires active pullup to +5V (V <sub>dc</sub> ).	(Internal Driver)  VCTL O  5V Zener 4700  -5V (Internal)	
6	Vdc	Supply voltage		